

● General Description

It combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

● Features

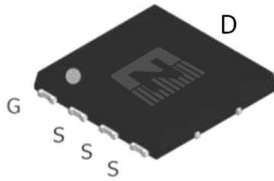
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low thermal resistance
- AEC-Q101 qualified

● Application

- BLDC motor driver
- DC-DC
- Load switch



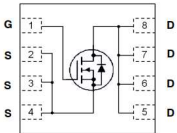
● Product Summary



DFN8*8

● Ordering Information

Part NO.	ZMSA009N08HG
Marking	ZMS009N08H
Packing information	REEL TAPE
Basic ordering unit (pcs)	2500



$V_{DS}=80V$

$R_{DS(ON)}=0.86m\Omega$

$I_D=507A$



● Absolute Maximum Ratings ($T_A=25^\circ C$, unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Max.	Unit
Drain-source voltage	V_{DS}	$25^\circ C \leq T_J \leq 175^\circ C$	-	80	V
Gate-source voltage ^①	V_{GS}	DC; $-55^\circ C \leq T_J \leq 175^\circ C$	-20	20	V
Continuous drain current	I_D	$V_{GS}=10V, T_C=25^\circ C$	-	507	A
	I_D	$V_{GS}=10V, T_C=75^\circ C$	-	414	A
	I_D	$V_{GS}=10V, T_C=100^\circ C$	-	359	A
Pulsed drain current	I_{DM}	Pulsed; $t_p \leq 10 \mu s; T_C = 25^\circ C$;	-	2028	A
Diode continuous current	I_S	$V_{GS}=0V, T_C=25^\circ C$	-	462	A
Diode pulse current	$I_{S,pulse}$	Pulsed; $t_p \leq 10 \mu s; T_C = 25^\circ C$;	-	1848	A
Total power dissipation	P_D	$V_{GS} > 6V, T_C=25^\circ C$	-	600	W
Total power dissipation	P_D	$V_{GS} > 6V, T_A=25^\circ C$	-	4.3	W
Operating junction temperature	T_J		-55	175	$^\circ C$
Storage temperature	T_{STG}		-55	175	$^\circ C$
Single pulse avalanche energy	E_{AS}	$L=0.1mH, V_{GS}=10V, R_g=25\Omega$	-	776	mJ

Single pulse avalanche energy	E_{AS}	$L=0.5\text{mH}$, $V_{GS}=10\text{V}$, $R_g=25\Omega$	-	1560	mJ
ESD level (HBM)	CLASS 2				

● Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}	-	-	0.25	$^{\circ}\text{C/W}$
Thermal resistance, junction - ambient	$R_{thJA}^{(2)}$	-	-	35	$^{\circ}\text{C/W}$
Soldering temperature	T_{sold}	-	-	260	$^{\circ}\text{C}$

● Electronic Characteristics ($T_j=25^{\circ}\text{C}$, unless otherwise specified)

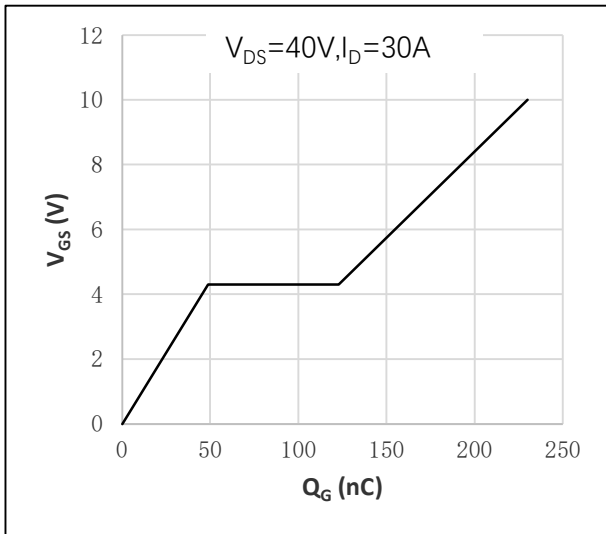
Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Drain-source breakdown voltage	BV_{DSS}	$V_{GS}=0\text{V}$, $I_D=250\mu\text{A}$, $T_j=25^{\circ}\text{C}$	80	-	-	V
		$V_{GS}=0\text{V}$, $I_D=1\text{mA}$, $T_j=-55^{\circ}\text{C}$	76.7	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{GS}=V_{DS}$, $I_D=250\mu\text{A}$, $T_j=25^{\circ}\text{C}$	2	2.9	4	V
		$V_{GS}=V_{DS}$, $I_D=1\text{mA}$, $T_j=-55^{\circ}\text{C}$	-	-	4.6	V
		$V_{GS}=V_{DS}$, $I_D=1\text{mA}$, $T_j=175^{\circ}\text{C}$	1.2	-	-	V
Drain-source leakage current	I_{DSS}	$V_{GS}=0\text{V}$, $V_{DS}=80\text{V}$, $T_j=25^{\circ}\text{C}$	-	-	1	μA
		$V_{GS}=0\text{V}$, $V_{DS}=80\text{V}$, $T_j=175^{\circ}\text{C}$	-	-	500	μA
Gate- source leakage current	I_{GSS}	$V_{GS}=\pm 20\text{V}$, $V_{DS}=0\text{V}$	-	-	± 100	nA
Static drain-source on resistance	$R_{DS(ON)}$	$V_{GS}=10\text{V}$, $I_D=30\text{A}$, $T_j=25^{\circ}\text{C}$	-	0.86	1.08	m Ω
		$V_{GS}=10\text{V}$, $I_D=30\text{A}$, $T_j=175^{\circ}\text{C}$	-	1.86	-	m Ω
Forward transconductance	g_{FS}	$V_{DS}=5\text{V}$, $I_{SD}=10\text{A}$	-	35	-	S
Diode forward voltage	V_{FSD}	$V_{GS}=0\text{V}$, $I_{SD}=30\text{A}$	-	0.8	1.3	V

● Dynamic characteristics ($T_j=25^{\circ}\text{C}$, unless otherwise specified)

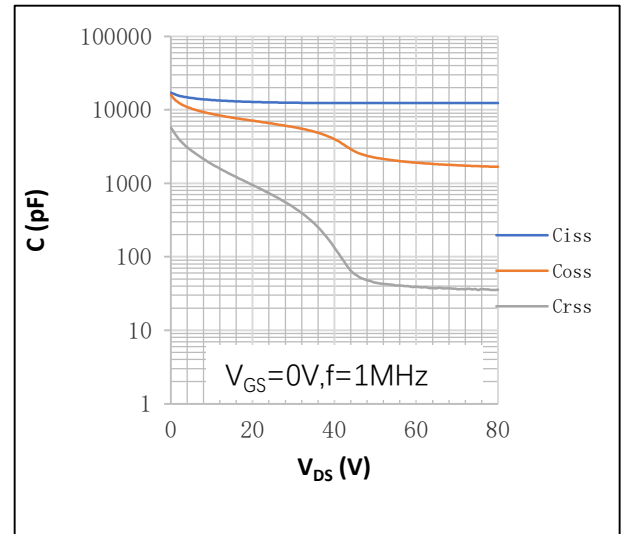
Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Input capacitance	C_{iss}	$f=1\text{MHz}$, $V_{DS}=40\text{V}$, $V_{GS}=0\text{V}$	-	12407	-	pF
Output capacitance	C_{oss}		-	3897	-	pF
Reverse transfer capacitance	C_{rss}		-	125	-	pF
Gate resistance	R_g	$f=1\text{MHz}$	-	1.6	-	Ω
Total gate charge	Q_g	$V_{DD}=40\text{V}$, $I_D=30\text{A}$, $V_{GS}=10\text{V}$	-	229.9	-	nC
Gate-source charge	Q_{gs}		-	48.9	-	nC
Gate-drain charge	Q_{gd}		-	74.1	-	nC

Turn-on delay time	$t_{D(on)}$	$V_{GS}=10V, V_{DS}=40V,$ $R_G=3.3\Omega, I_D=30A$	-	35	-	ns
Turn-on rise time	t_r		-	18	-	ns
Turn-off delay time	$t_{D(off)}$		-	74	-	ns
Turn-off fall time	t_f		-	23	-	ns
Reverse recovery time	t_{rr}	$V_{DD}=40V, di_s/dt = 100A/\mu s,$ $I_S=30A$	-	96	-	ns
Reverse recovery charge	Q_{rr}		-	192	-	nC

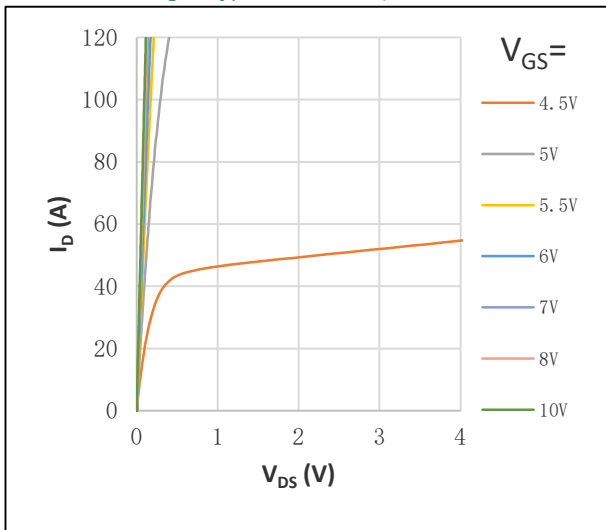
● Fig.1 Gate-source voltage as a function of gate charge; Typical values; $T_j=25^\circ\text{C}$



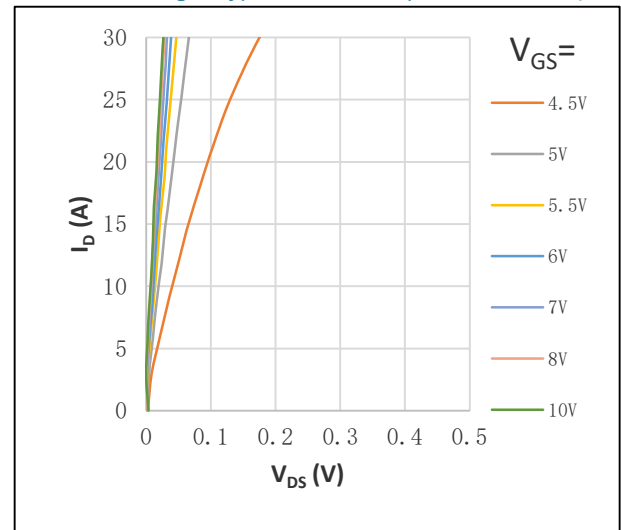
● Fig.2 Input, output and reverse transfer capacitances as a function of drain-source voltage; Typical values; $T_j=25^\circ\text{C}$



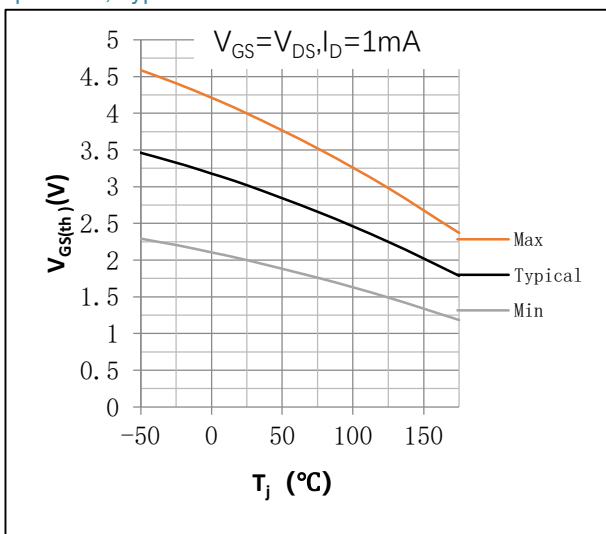
● Fig.3 Output characteristics: drain current as a function of drain-source voltage; Typical values; $T_j=25^\circ\text{C}$



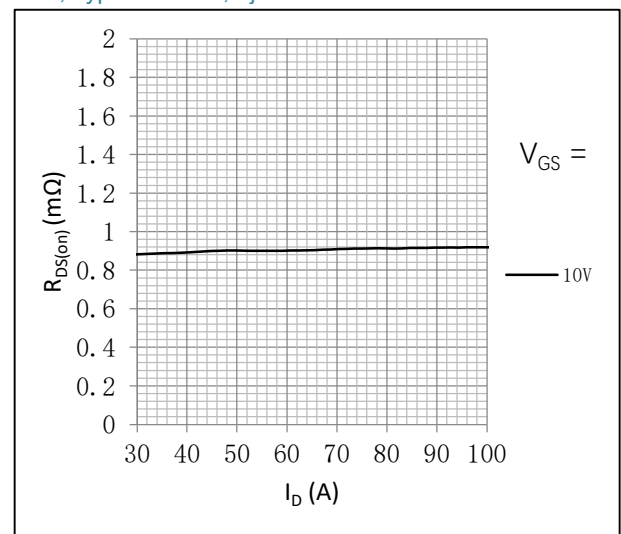
● Fig.4 Output characteristics: drain current as a function of drain-source voltage; Typical values: Expanded curve; $T_j=25^\circ\text{C}$



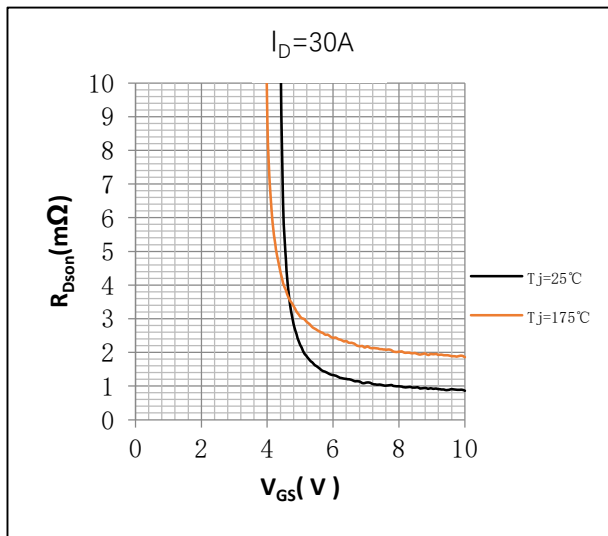
● Fig.5 Gate-source threshold voltage as a function of junction temperature; Typical/Min/Max values



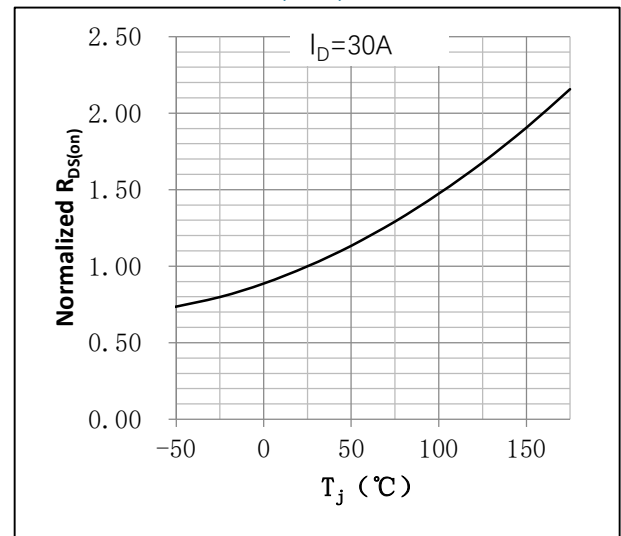
● Fig.6 Drain-source on-state resistance as a function of drain current; Typical values; $T_j=25^\circ\text{C}$



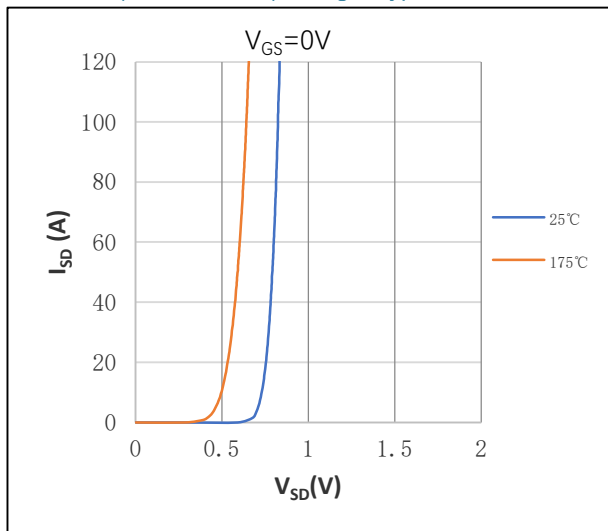
● Fig.7 Drain-source on-state resistance as a function of gate-source voltage; Typical values



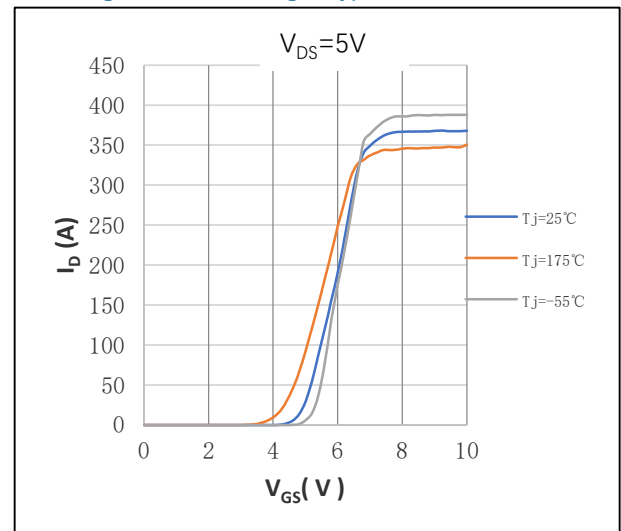
● Fig.8 Normalized drain-source on-state resistance factor as a function of junction temperature; Typical values Normalized On-Resistance= $R_{DS(on)}/R_{DS(on)}(25^{\circ}\text{C})$



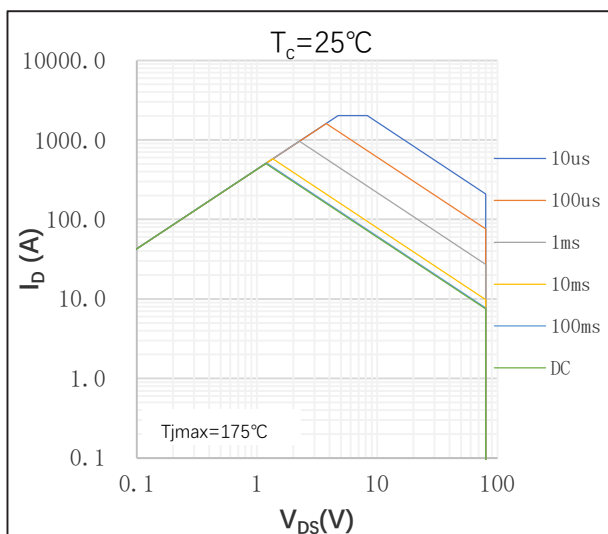
● Figure 9. Source (diode forward) current as a function of source-drain (diode forward) voltage; Typical values



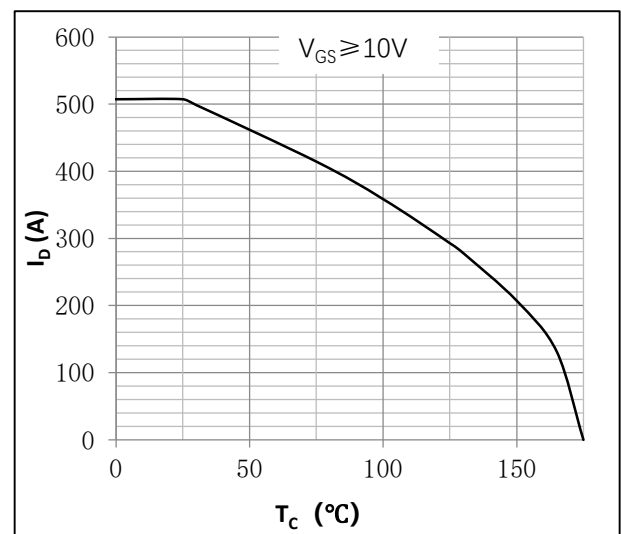
● Figure 10. Transfer characteristics: drain current as a function of gate-source voltage; Typical values



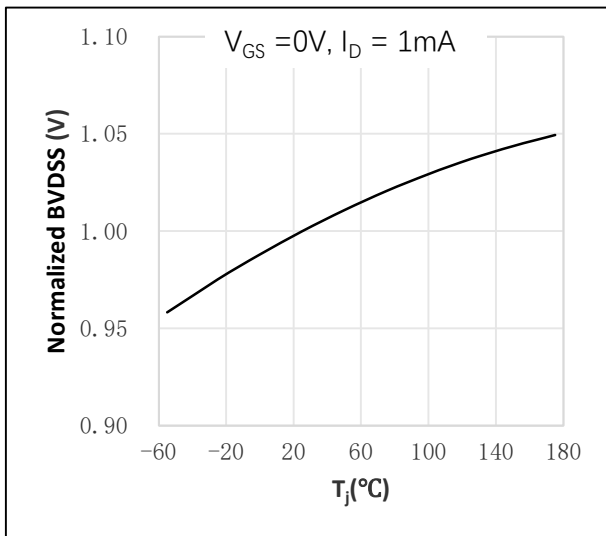
● Fig.11 Safe operating area: continuous and peak drain currents as a function of drain-source voltage; Calculative values



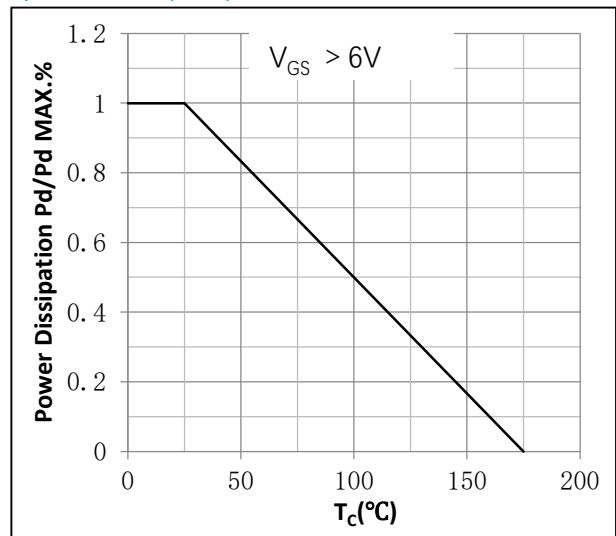
● Fig.12 Continuous drain current as a function of case temperature³; Calculative values



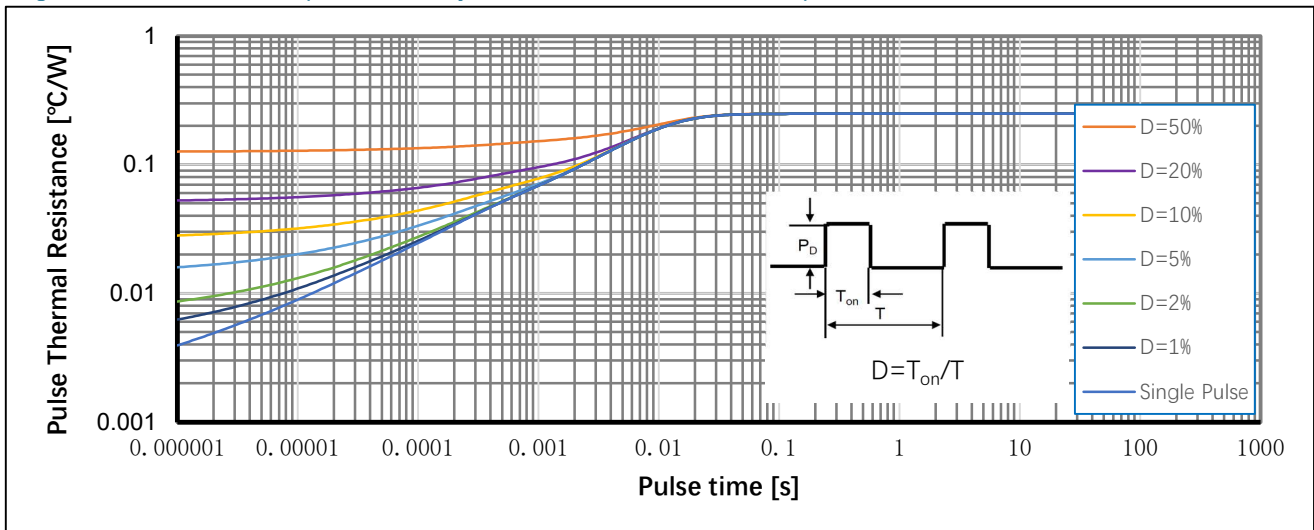
● Fig.13 Drain-source breakdown voltage as a function of junction temperature; Min values



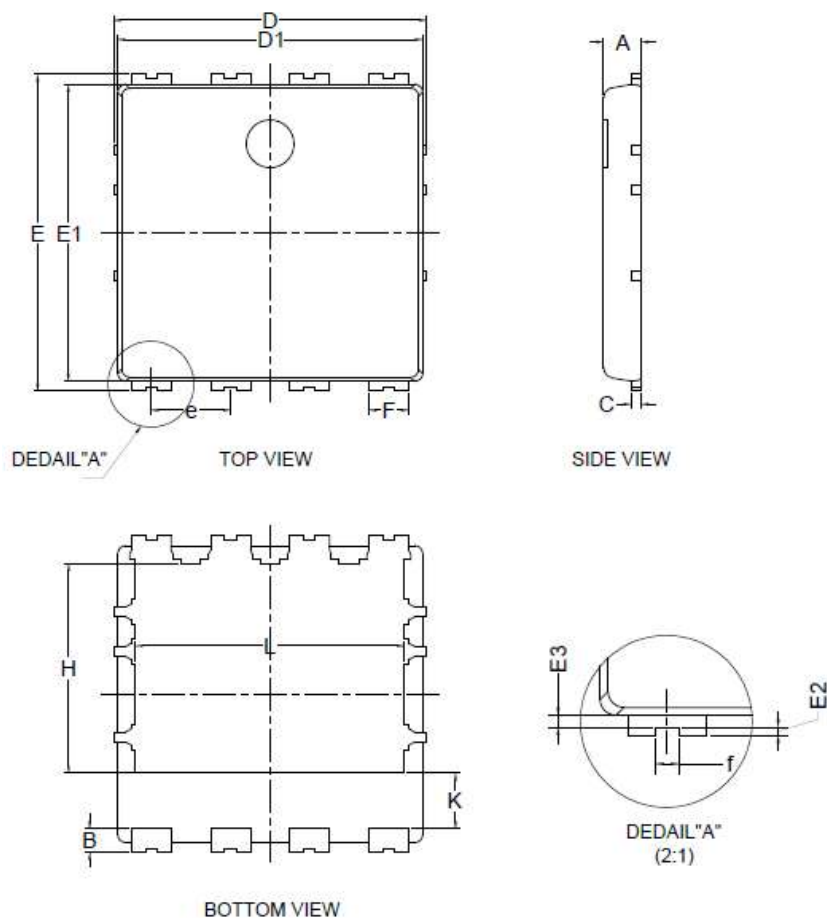
● Fig.14 Normalized total power dissipation as a function of case temperature; Calculative values Normalized Power Dissipation $= P_d / P_d(25^\circ C)$



● Fig.15 Transient thermal impedance from junction to case as a function of pulse duration; max values



● Package Outline



MILLIMETERS			
DIM	MIN	TYP	MAX
A	0.90	0.95	1.00
B	0.50	0.60	0.70
C	0.254TYP		
D	7.80	7.90	8.00
D1	7.60	7.70	7.80
E	7.90	8.00	8.10
E1	7.40	7.50	7.60
e	2.00TYP		
F	1.00TYP		
H	5.15	5.30	5.40
L	6.60	6.80	6.90
K	1.20	—	—
E2	0.04	0.10	0.16
E3	0.10	0.15	0.20
f	0.25	0.30	0.35

● Note

- ① Pulse : $V_{GS}=+20V/-20V$, Duty cycle=50%, $T_j=175^{\circ}C$, $t=1000$ hours; For DC, the following test conditions can be passed: $V_{GS}=+20V/-10V$, $T_j=175^{\circ}C$, $t=1000$ hours;
- ② Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate;
- ③ Practically the current will be limited by PCB, thermal design and operating temperature. $V_{GS}=10V$.

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● Revision History

Version	Date	Change
A	2022/7/6	New
B	2022/11/5	1.Add Reach, HF figure 2.ID figure modify 3.Rdson limit modify
C	2024/7/25	SOA curve Modified
D	2026/7/16	Apply new datasheet format.
E	2026/8/11	Update RthJC,ID,SOA.